





E2000 Horizontal Production Furnace

equipment

process

solutions

Designed for low cost productivity and furnace platform flexibility

The design of the centrotherm E 2000 system supports the multiple process capability needs of a maximum capacity, high process performance user and provides all the features of full production in a full size, easy-to-maintain, safe and reliable horizontal furnace platform.

The centrotherm design is outstanding for high performance, small footprint and low cost of ownership while offering high process flexibility required for multiple applications.

Processes

Features

and Benefits

Atmospheric Processes

Diffusion Curing

BBr₃-, B₂H₆-Doping Activation Annealing POCl₃-Doping Silicidation H₂-, N₂-Annealing Nitridation Wet-, Dry-Oxidation [Option: DCE, HCI] Contact Sintering

LPCVD Processes

Polysilicon TOMCAT
Polysilicon-Doping LTO
Silicon Nitride HTO
Oxinitride SIPOS

TEOS Low pressure deposition

of passivation

PECVD Processes

PECVD-Oxide PECVD-Nitride PECVD-Oxinitride

up to 4 stacked quartz or SiC tube reactor chambers [up to 300 mm 4 stack possible]

- process selectable chamber options available
- fully automated cassette-to-cassette loading for processing up to 200 mm wafers
- advanced water cooling system: no thermal interference between different tubes, no consumption of clean room air
- clean automated boat loading for premium processing of up to 200 mm wafers
 - modular component design for ease of installation and start up in clean room facilities



centrotherm E2000



Fully automated cassette-to-cassette production up to 200 wafers per tube

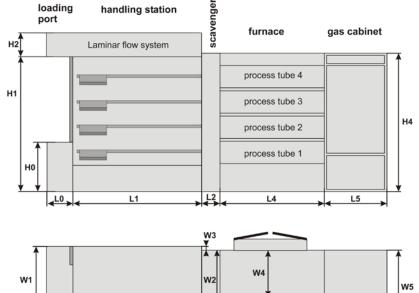


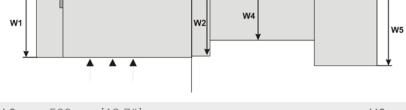
Horizontal Furnace for High Process Performance

centrotherm

E2000 Horizontal Production Furnace

Dimensions





LO:	500 mm [19.7"]			H0:	950 mm [37.4"]
L1:	2520 mm [99.2"]	W1:	1310 mm [52.8"]	H1:	2680 mm [105.5"]
L2:	350 mm [13.8"]	W2:	1225 mm [48.3"]	H2:	520 mm [20.5"]
		W3:	145 mm [5.7"]		
L4:	2000 mm [78.7"]	W4:	800 mm [31.5"]	H4:	2650 mm [104.3"]
L5:	1200 mm [47.2"]	W5:	1400 mm [55.1"]		

Preliminary size | | real dimensions in customized layout | | customized dimensions upon request

Technical Data

Wafer sizes 150 mm [max. 200 wafers] 200 mm [max. 150 wafers] | 300 mm [max. 75 wafers] 3 or 5 zone 900 mm to 1000 mm flat zone Heating system ± 0.5 °C across flat zone 200 °C to 1300 °C Process temperature Possible process gases H₂, Ar, O₂, N₂O, N₂, SiH₄, NH₃, B₂H₆, PH₃, SiH₂Cl₂ Power consumption 95 kW [heating cassette with Ø 290 mm at 1000 °C] Power supply 400 V, 140 A [system will be modified to country-specific power supply] Dry air 600 - 1000 kPa Cooling water 50 - 70 LPM **Exhaust** 200 m³/h per tube

centrotherm

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Options

boat elevator and wafer handling automation